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(54) Title: MICRO CHIP

(57) Abstract: Instant invention is about a micro chip comprising plurality of layers of LTCC wherein a reaction chamber is formed in plurality of top layers to load samples. A heater embedded in atleast one of the layers below the reaction chamber and a temperature sensor is embedded in atleast one of the layers between the heater and the reaction chamber for analyzing the sample. The temperature sensor can be placed outside the chip to measure the chip temperature.



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